

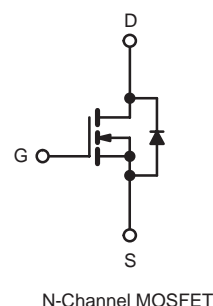
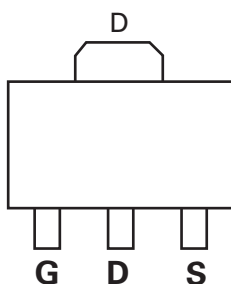
N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.030 at $V_{GS} = 10$ V	8.0
	0.034 at $V_{GS} = 4.5$ V	6.5

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT


ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	60		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C) ^a	T _A = 25 °C	I _D	8.0	7.0	A
	T _A = 70 °C		6.4	5.6	
Pulsed Drain Current		I _{DM}	40		
Avalanche Current		I _{AS}	15		
Single Pulse Avalanche Energy		E _{AS}	11		mJ
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.3	1.7	W
	T _A = 70 °C		2.3	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	- 55 to 175		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	36	45	°C/W
		75	90	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

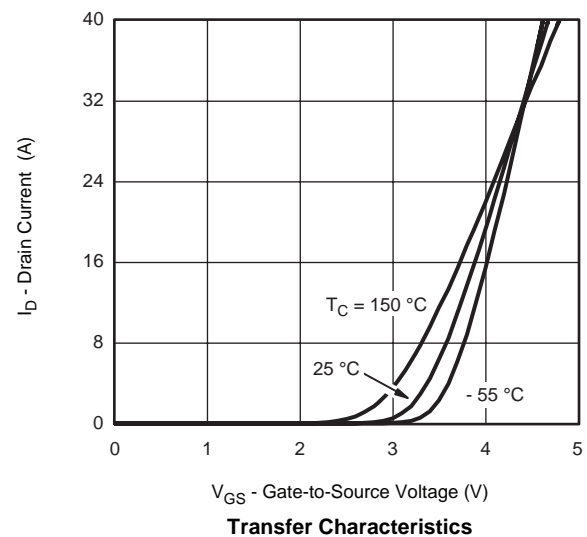
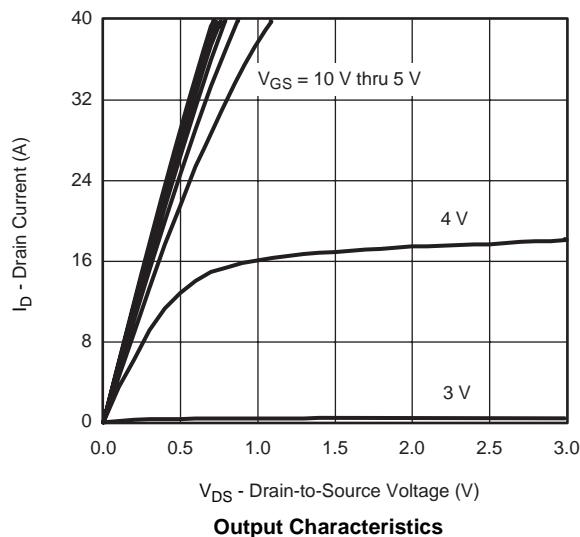
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$			20	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		0.030		Ω
		$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.035		
		$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.040		
		$V_{GS} = 4.5\text{ V}, I_D = 5.1\text{ A}$		0.034		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6.0\text{ A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		18	27	nC
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			5.3		
Gate Resistance	R_g	$V_{GS} = 0.1\text{ V}, f = 5\text{ MHz}$	0.5	1.4	2.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		10	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	t_f			12	24	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	80	

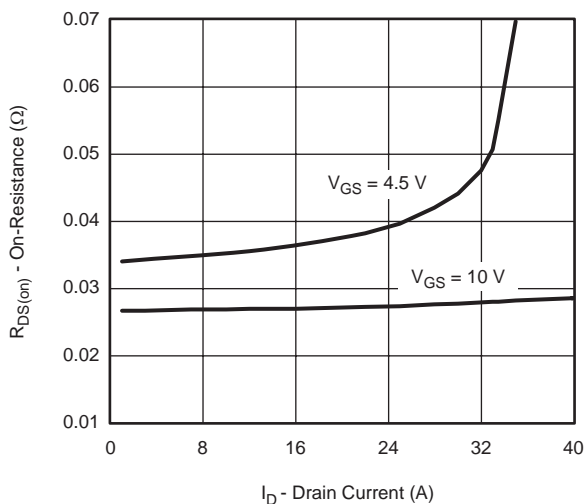
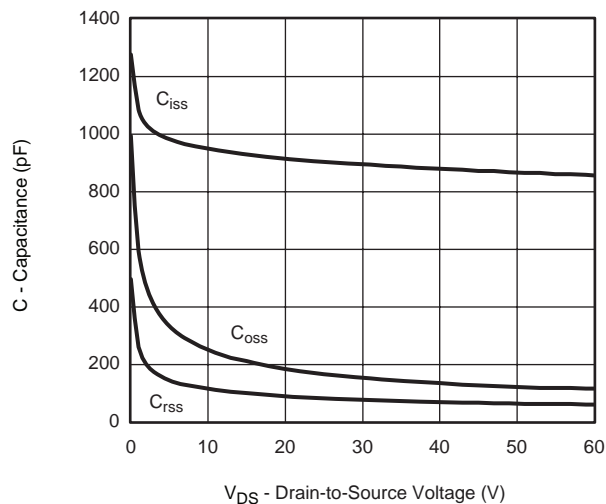
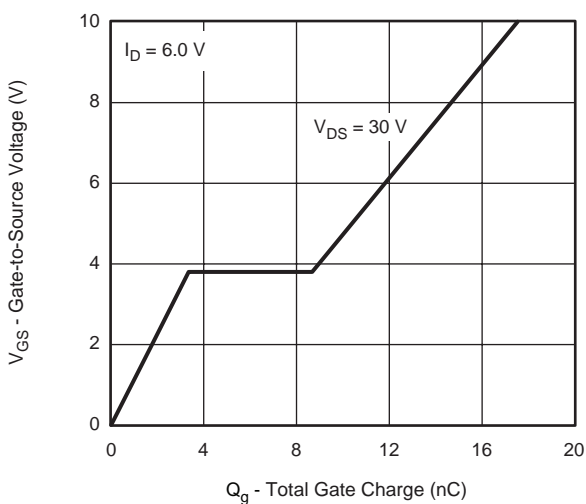
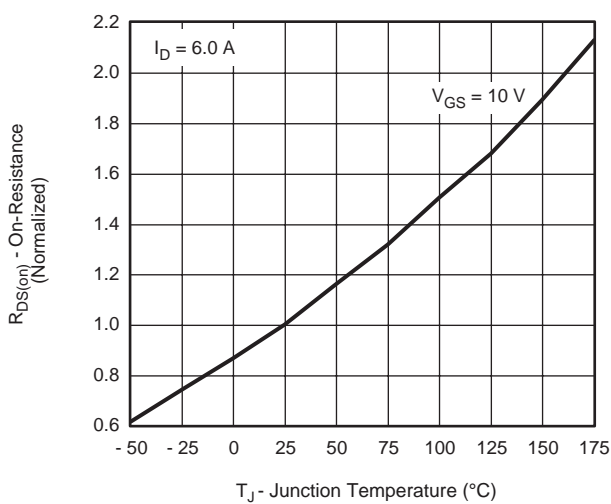
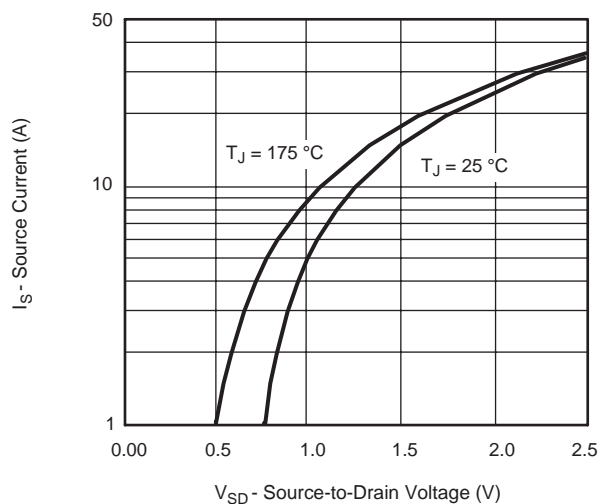
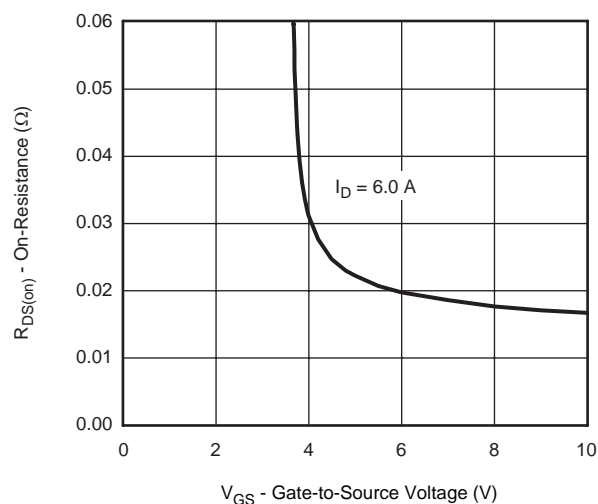
Notes:

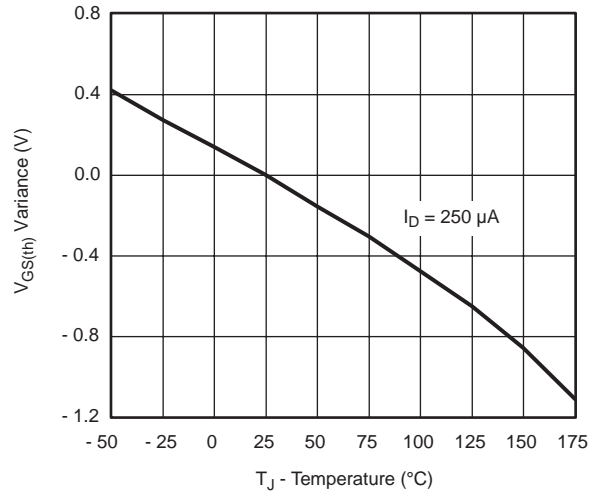
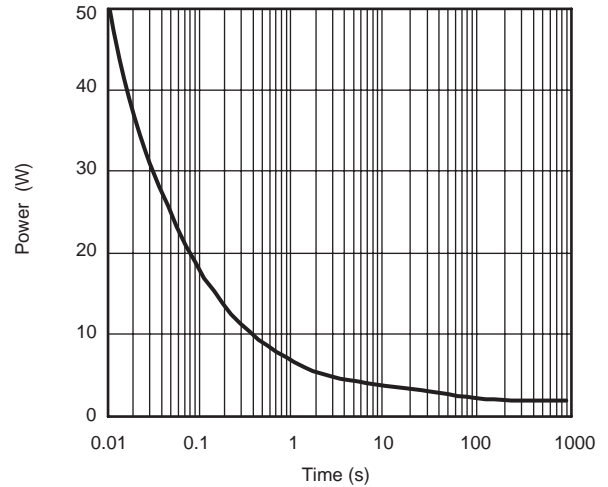
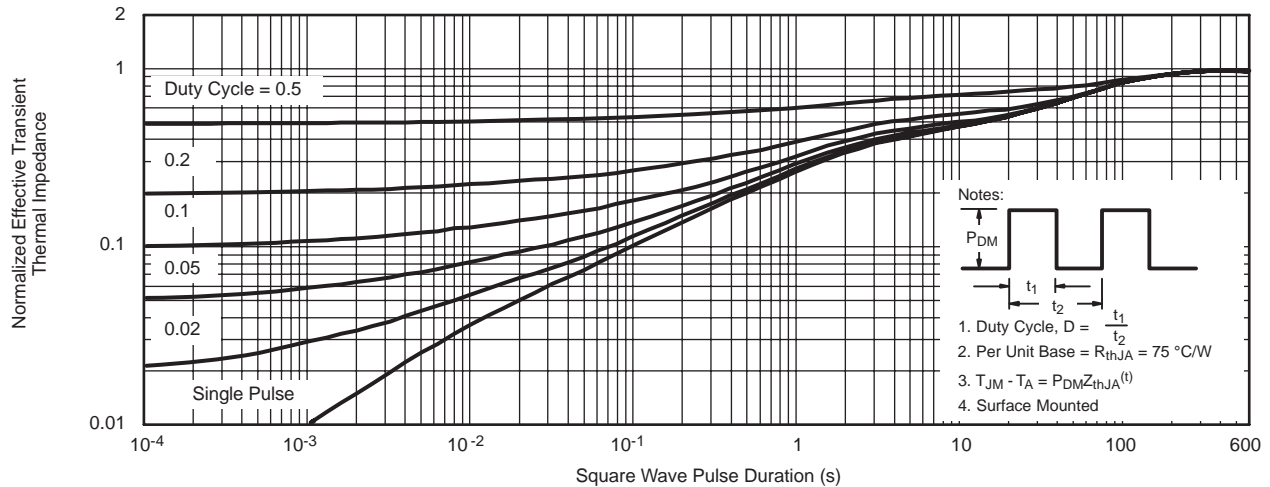
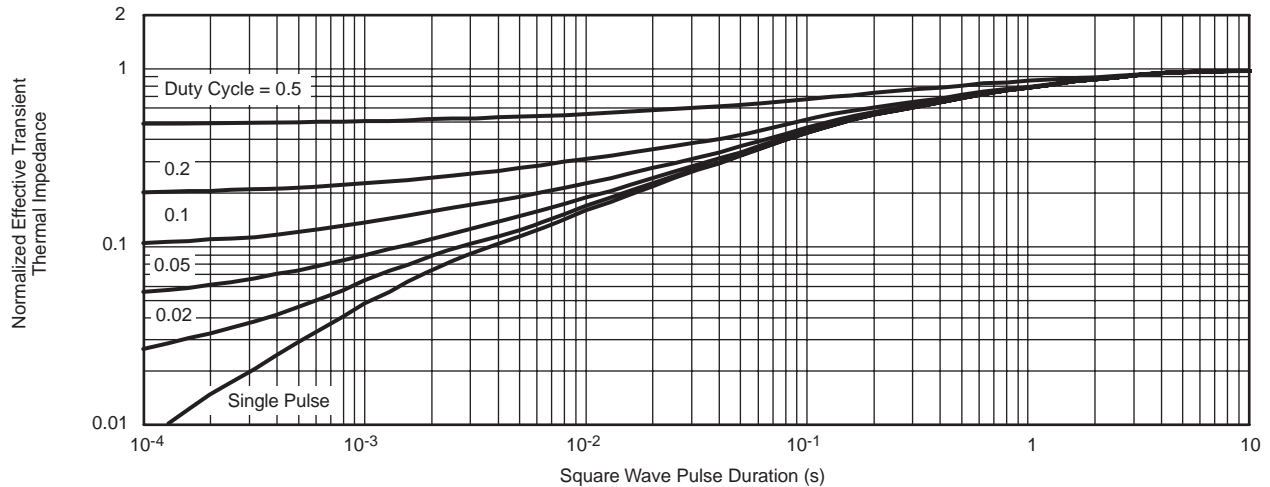
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

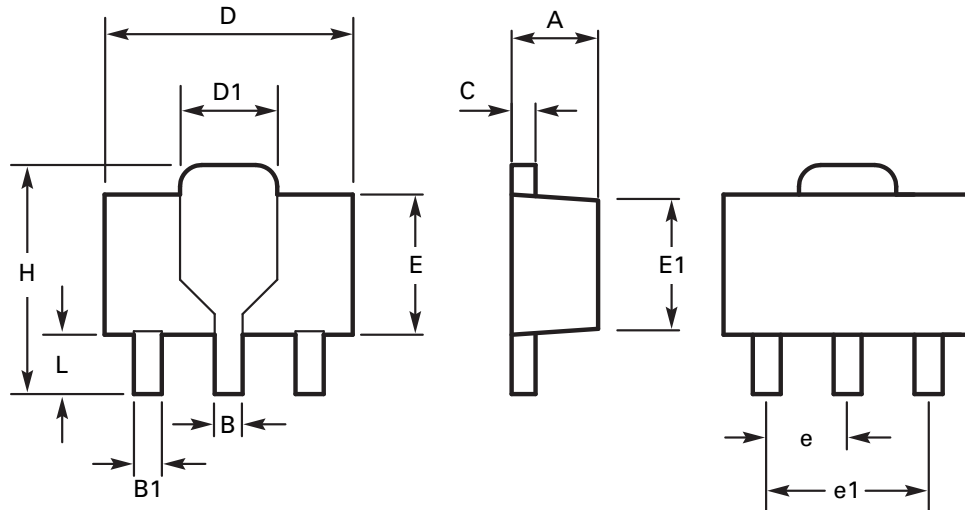
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Threshold Voltage

Single Pulse Power

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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